IXYS

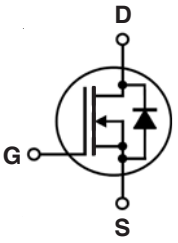
Preliminary Technical Information

Depletion Mode MOSFET

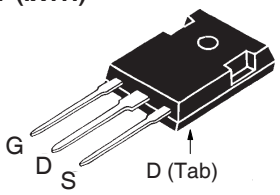
IXTH10N100D2
IXTT10N100D2

V_{DSX} = 1000V
$I_{D(on)}$ ≥ 10A
$R_{DS(on)}$ ≤ 1.5Ω

N-Channel

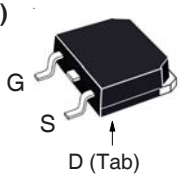


TO-247 (IXTH)



Symbol	Test Conditions	Maximum Ratings	
V_{DSX}	T_J = 25°C to 150°C	1000	V
V_{DGX}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	1000	V
V_{GSX}	Continuous	±20	V
V_{GSM}	Transient	±30	V
P_D	T_C = 25°C	695	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-268 (IXTT)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSX}	V_{GS} = - 5V, I_D = 250μA	1000			V
$V_{GS(off)}$	V_{DS} = 25V, I_D = 1mA	- 2.5		- 4.5	V
I_{GSX}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
$I_{DSX(off)}$	V_{DS} = V_{DSX}, V_{GS} = - 5V			10	μA
	T_J = 125°C			250	μA
$R_{DS(on)}$	V_{GS} = 0V, I_D = 5A, Note 1			1.5	Ω
$I_{D(on)}$	V_{GS} = 0V, V_{DS} = 25V, Note 1	10			A

Features

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Audio Amplifiers
- Start-up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 30V, I_D = 5A, Note 1	11	17		S
C_{iss}	V_{GS} = -10V, V_{DS} = 25V, f = 1MHz		5320		pF
C_{oss}			300		pF
C_{rss}			70		pF
$t_{d(on)}$	**Resistive Switching Times**		33		ns
t_r	V_{GS} = ± 5V, V_{DS} = 500V, I_D = 5A		36		ns
$t_{d(off)}$	R_G = 3.3Ω (External)		33		ns
t_f			164		ns
$Q_{g(on)}$	V_{GS} = ± 5V, V_{DS} = 500V, I_D = 5A		200		nC
Q_{gs}			19		nC
Q_{gd}			98		nC
R_{thJC}				0.18	°C/W
R_{thCS}	TO-247		0.21		°C/W

Safe-Operating-Area Specification

Symbol	Test Conditions	Characteristic Values Min.	Typ.	Max.	
SOA	V_{DS} = 800V, I_D = 0.22A, T_C = 75°C, tp = 5s	176			W

Source-Drain Diode

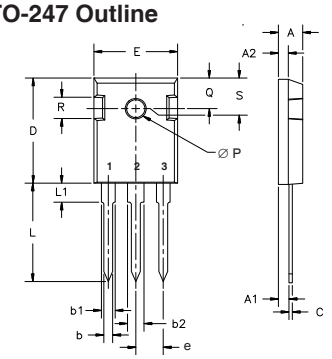
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
V_{SD}	I_F = 10A, V_{GS} = -10V, Note 1		0.8	1.3	V
t_{rr}	I_F = 5A, -di/dt = 100A/µs		1.2		µs
I_{RM}	V_R = 100V, V_{GS} = -10V		23		A
Q_{RM}			13.8		µC

Note 1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

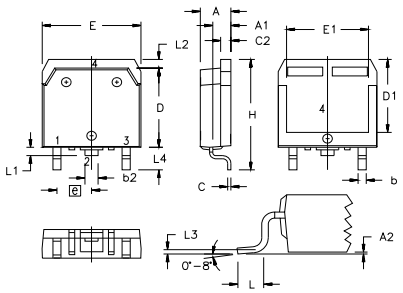
TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

TO-268 Outline



Terminals: 1 - Gate 2,4 - Drain
3 - Source

SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25°C

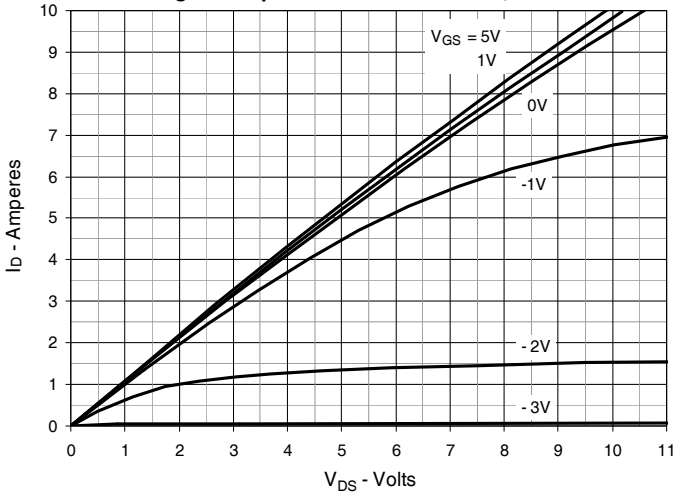


Fig. 2. Extended Output Characteristics @ T_J = 25°C

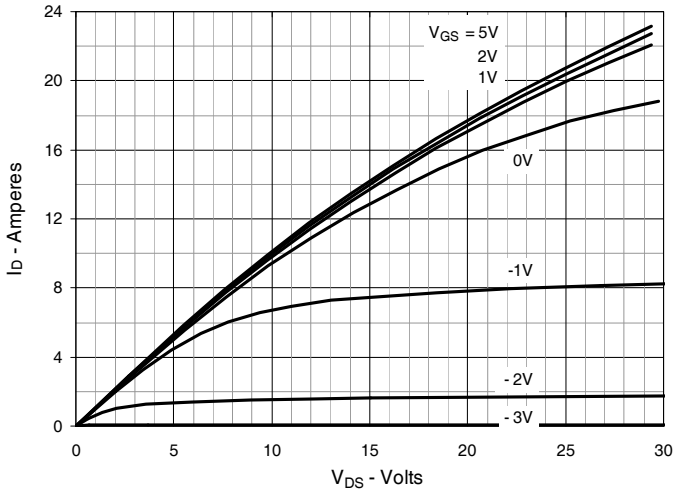


Fig. 3. Output Characteristics @ T_J = 125°C

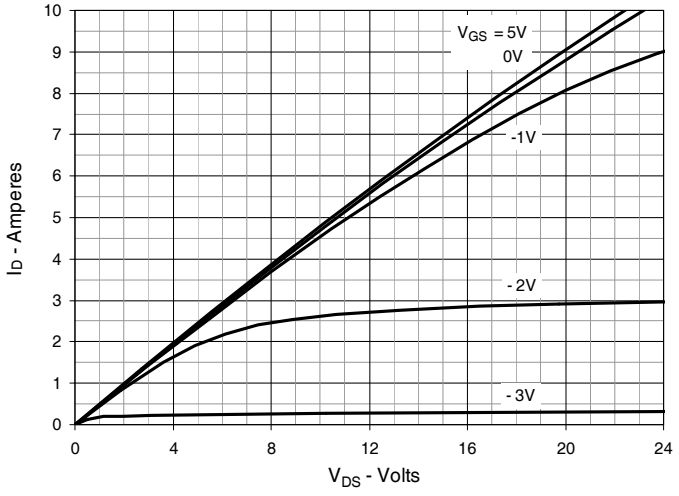


Fig. 4. Drain Current @ T_J = 25°C

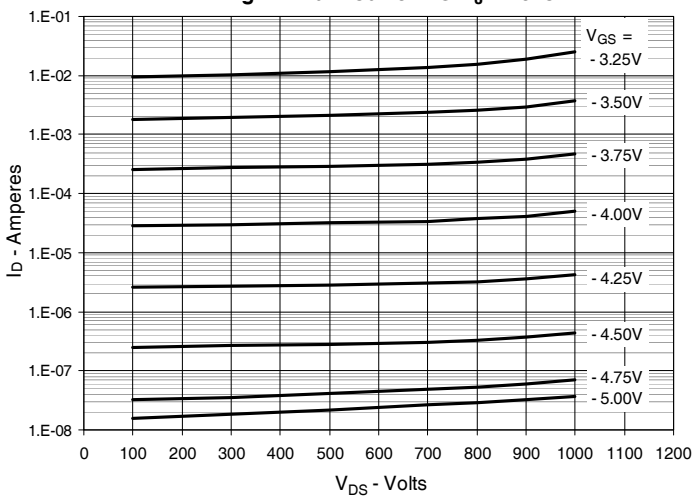


Fig. 5. Drain Current @ T_J = 100°C

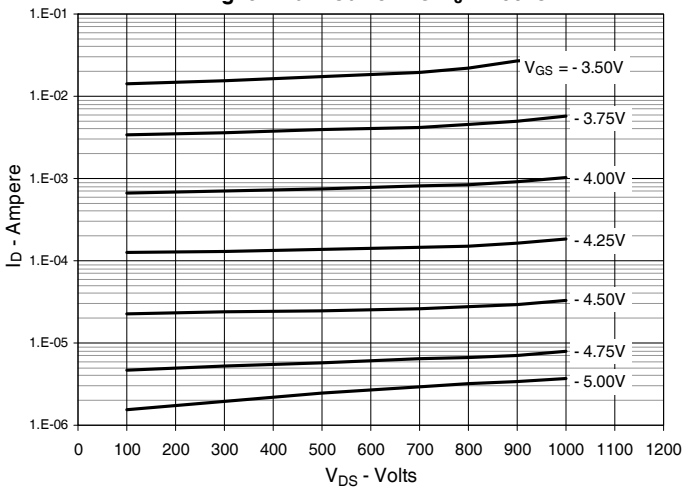
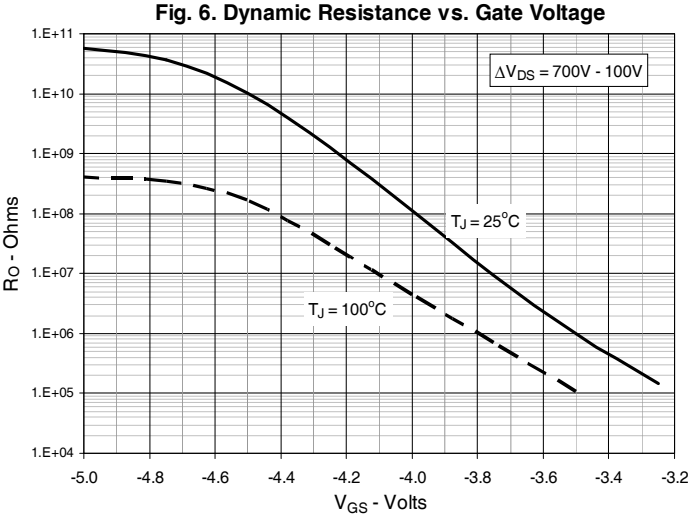


Fig. 6. Dynamic Resistance vs. Gate Voltage



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Fig. 7. Normalized $R_{DS(on)}$ vs. Junction Temperature

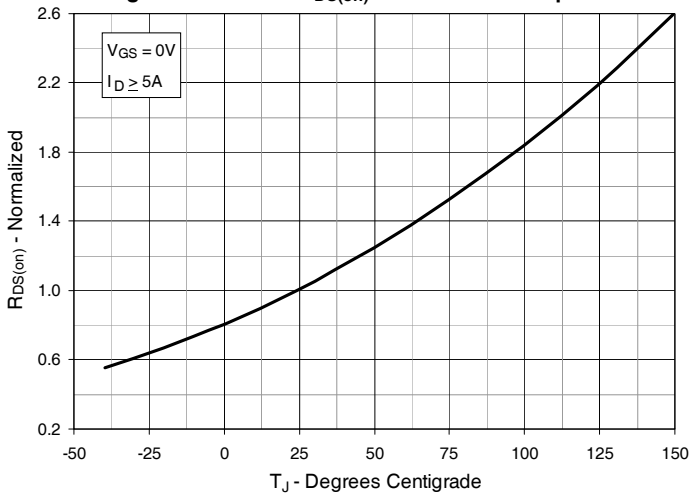


Fig. 8. $R_{DS(on)}$ Normalized to I_D = 5A Value vs. Drain Current

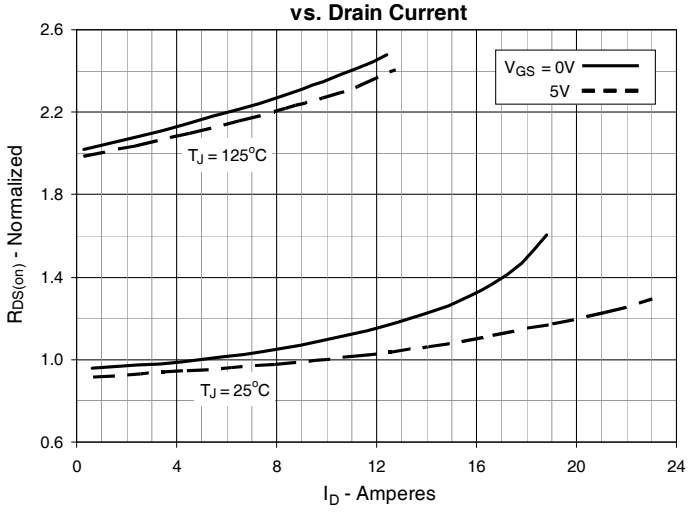


Fig. 9. Input Admittance

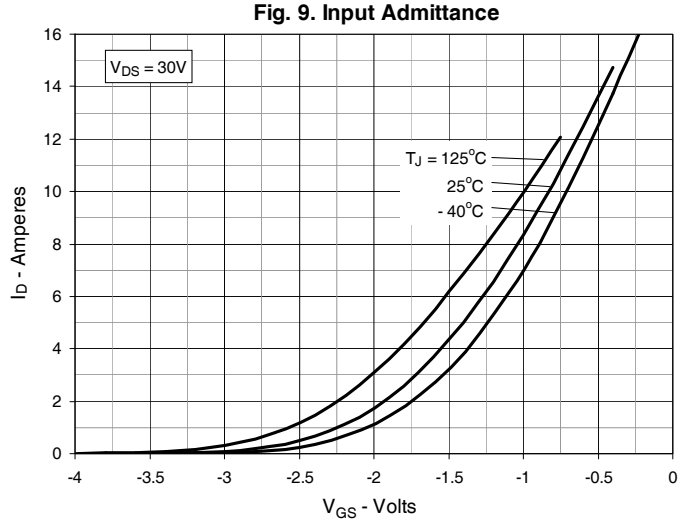


Fig. 10. Transconductance

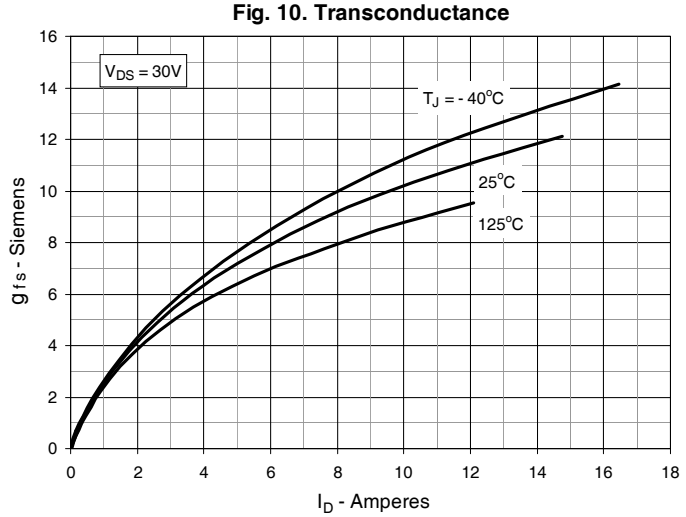


Fig. 11. Normalized Breakdown and Threshold Voltages vs. Junction Temperature

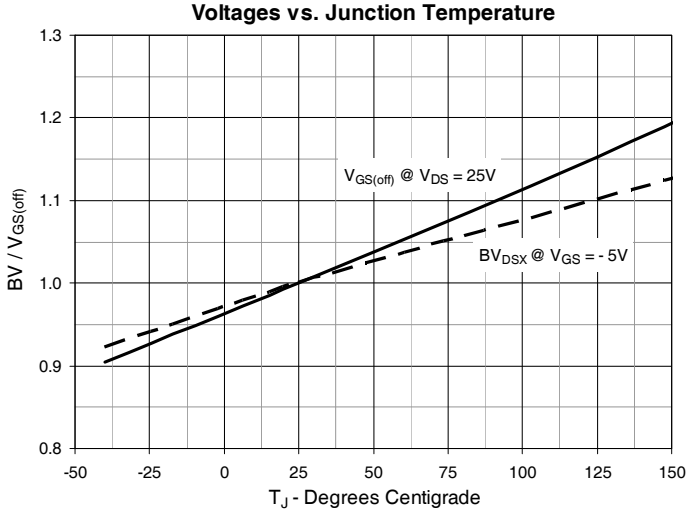
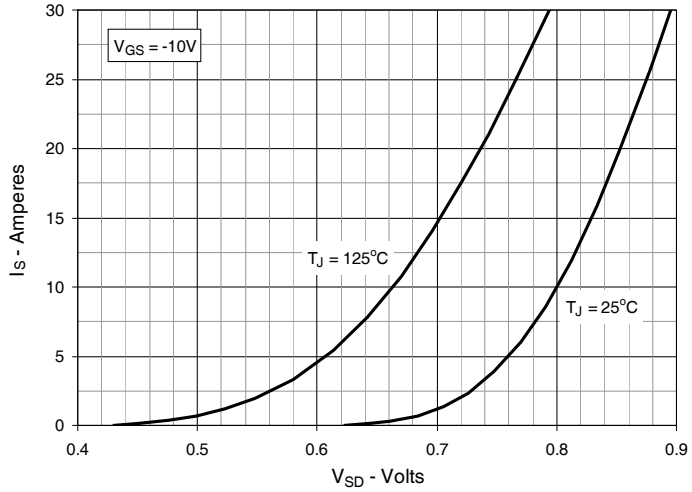


Fig. 12. Forward Voltage Drop of Intrinsic Diode



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 13. Capacitance

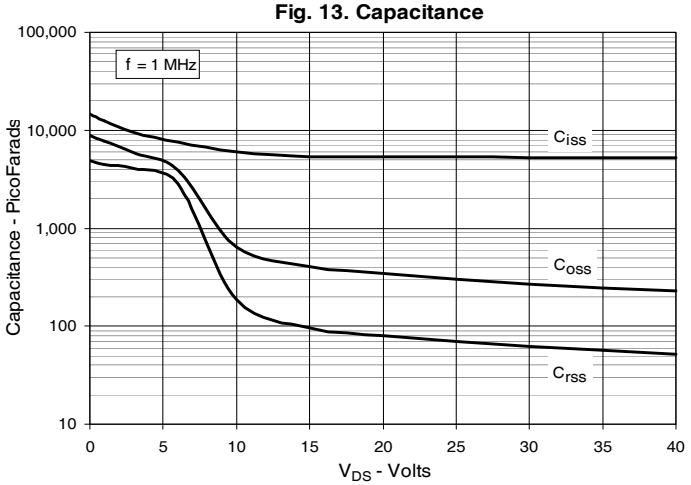


Fig. 14. Gate Charge

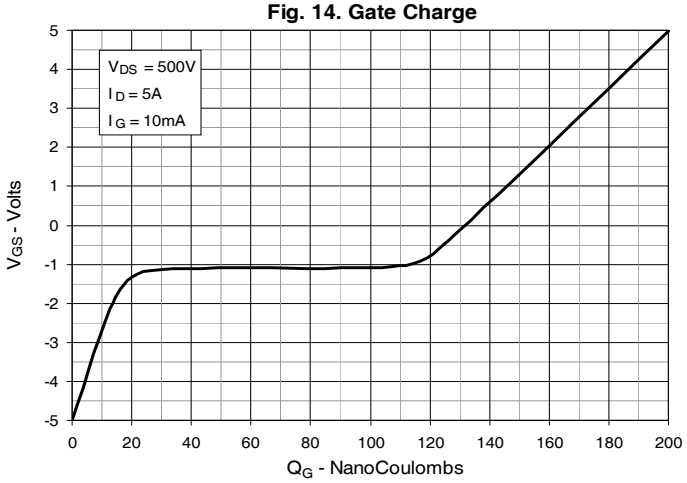


Fig. 15. Forward-Bias Safe Operating Area @ T_C = 25°C

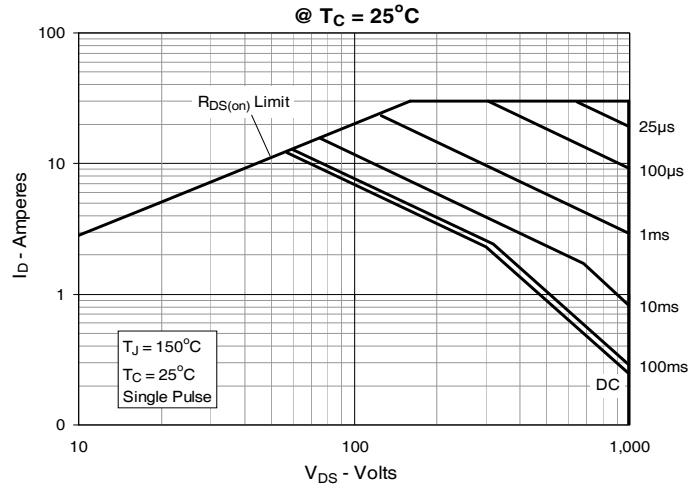


Fig. 16. Forward-Bias Safe Operating Area @ T_C = 75°C

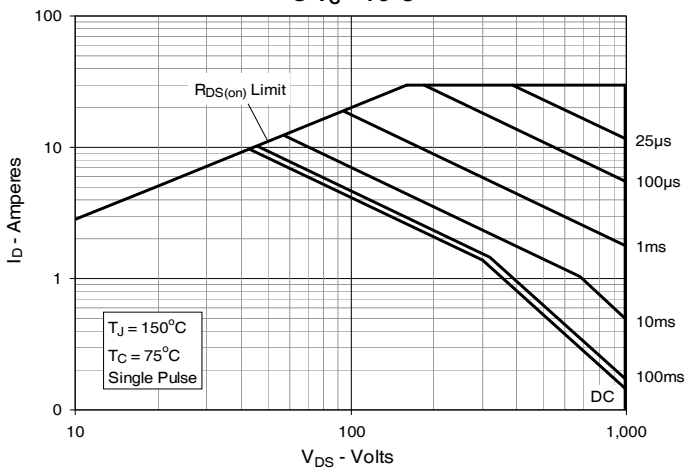
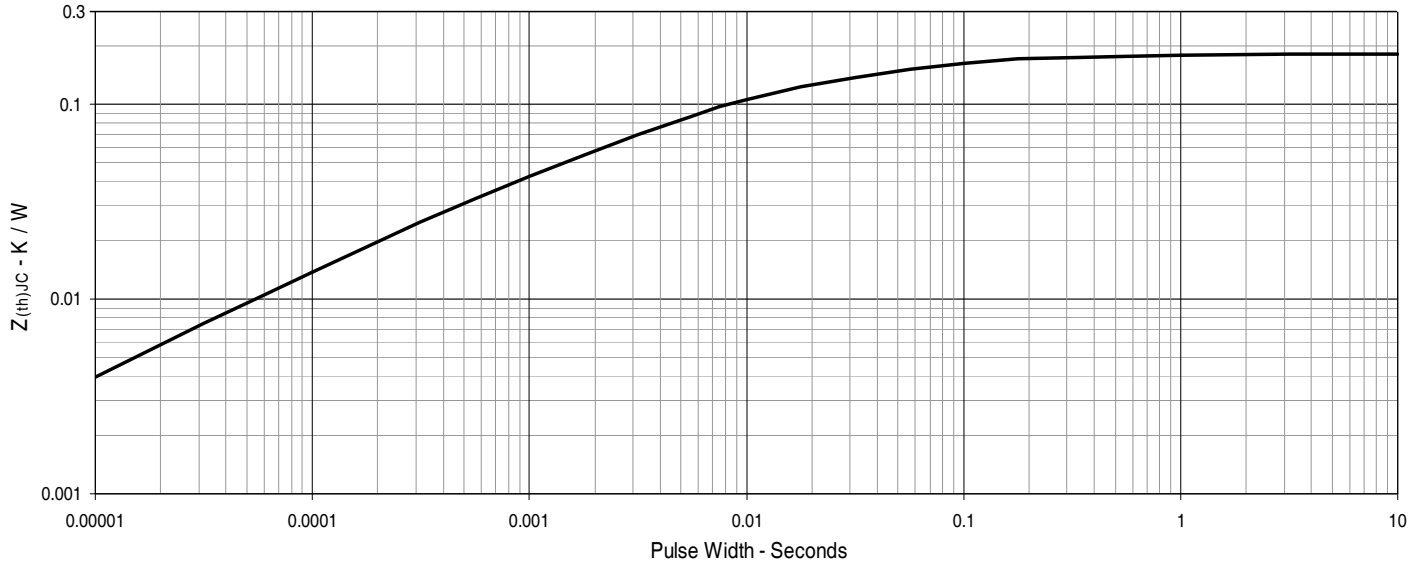


Fig. 17. Maximum Transient Thermal Impedance



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